

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently amended): A semiconductor device having a sealing structure for a semiconductor chip, comprising:

a plurality of main electrodes, at least some of the main electrodes being provided on each of at least two different main surfaces of the semiconductor chip;

a plurality of external electrodes electrically connected to the main electrodes via connection members, respectively;

a sealing member made of a glass based sealing material for encapsulating at least the semiconductor chip, the main electrodes and the connection members; and

a brazing member made of a silver based brazing material having a high fusing point, which is ~~provided for integrally connecting~~ connected between a part of the main electrodes and a part of the external electrodes,

wherein the semiconductor chip is of a wide gap type, and the fusing point of the glass based sealing material is lower than that of the silver based brazing material.

Claim 2 (Currently Amended): The semiconductor device according to claim 1, wherein the brazing material ~~serves as a passage for dissipating~~ is configured to dissipate heat to the outside.

Claim 3 (Currently amended): A semiconductor device having a sealing structure for a semiconductor chip, comprising:

a plurality of main electrodes, at least some of the main electrodes being provided on each of at least two different main surfaces of the semiconductor chip;

a plurality of external electrodes ~~directly~~ in direct physical contact with and electrically connected to the main electrodes by pressure contact, respectively; and

a sealing member made of a glass based sealing material ~~for encapsulating~~ configured to encapsulate at least the semiconductor chip, the main electrodes and connected portions of the external electrodes,

wherein the semiconductor chip is of a wide gap type.

Claim 4 (New): The semiconductor device according to Claim 1, wherein the semiconductor chip includes one of silicon carbide or gallium nitride.

Claim 5 (New): The semiconductor device according to Claim 3, wherein the semiconductor chip includes one of silicon carbide or gallium nitride.

Claim 6 (New): A semiconductor device having a sealing structure for a semiconductor chip, comprising:

a plurality of main electrodes, at least some of the main electrodes being provided on each of at least two different main surfaces of the semiconductor chip;

a plurality of external electrodes;

means for maintaining direct physical and electrical contact of at least one of the external electrodes with a corresponding at least one of the main electrodes by applying pressure thereto; and

a sealing member made of a glass based sealing material configured to encapsulate at least the semiconductor chip, the main electrodes and connected portions of the external electrodes,

wherein the semiconductor chip is of a wide gap type.

Claim 7. (New): The semiconductor device according to Claim 6, wherein the semiconductor chip includes one of silicon carbide or gallium nitride.